Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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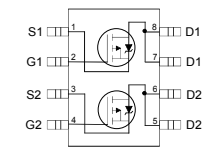
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Features

- Advanced Planar Technology
- Low On-Resistance
- Logic Level Gate Drive
- Dual P Channel MOSFET
- Dynamic dv/dt Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free, RoHS Compliant
- Automotive Qualified *



Top View

V_{DSS}	-55V
$R_{DS(on)}$ max.	0.105Ω
I_D	-3.4A


SO-8
AUIRF7342Q

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF7342Q	SO-8	Tape and Reel	4000	AUIRF7342QTR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	-55	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -10V	-3.4	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ -10V	-2.7	
I_{DM}	Pulsed Drain Current ①	-27	
P_D @T_A = 25°C	Maximum Power Dissipation ①	2.0	W
P_D @T_A = 70°C	Maximum Power Dissipation	1.3	
	Linear Dearating Factor	0.016	mW°/C
V_{GS}	Gate-to-Source Voltage	± 20	V
V_{GSM}	Gate-to-Source Voltage Single Pulse tp < 10µs	30	
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	114	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	62.5	°C/W

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*Qualification standards can be found at www.infineon.com

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	V_{GS} = 0V, I_D = -250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.054	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.095	0.105	Ω	V_{GS} = -10V, I_D = -3.4A ④
		—	0.150	0.170		V_{GS} = -4.5V, I_D = -2.7A ④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
gfs	Forward Trans conductance	3.3	—	—	S	V_{DS} = -10V, I_D = -3.1A
I_{DSS}	Drain-to-Source Leakage Current	—	—	-2.0	µA	V_{DS} = -55V, V_{GS} = 0V
		—	—	-25		V_{DS} = -55V,V_{GS} = 0V,T_J =55°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Q_g	Total Gate Charge	—	26	38	nC	I_D = -3.1A
Q_{gs}	Gate-to-Source Charge	—	3.0	4.5		V_{DS} = -44V
Q_{gd}	Gate-to-Drain Charge	—	8.4	13		V_{GS} = -10V, See Fig.10 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	22	ns	V_{DD} = -28V
t_r	Rise Time	—	10	15		I_D = -1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	43	64		R_G = 6.0Ω
t_f	Fall Time	—	22	32		R_D = 16Ω ④
C_{iss}	Input Capacitance	—	690	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	210	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	86	—		f = 1.0MHz, See Fig.9

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-27		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C,I_S = -2.0A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	54	80	ns	T_J = 25°C ,I_F = -2.0A,
Q_{rr}	Reverse Recovery Charge	—	85	130	nC	di/dt = 100A/µs ④

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)

② Starting T_J = 25°C, L = 20mH, R_G = 25Ω, I_{AS} = -3.4A. (See Fig. 8)

③ I_{SD} ≤ -3.4A, di/dt ≤ 150A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C.

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ When mounted on 1" square copper board , t < 10sec.

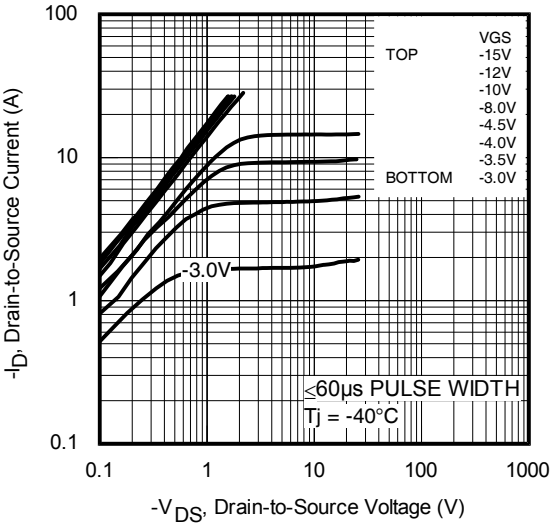


Fig. 1 Typical Output Characteristics

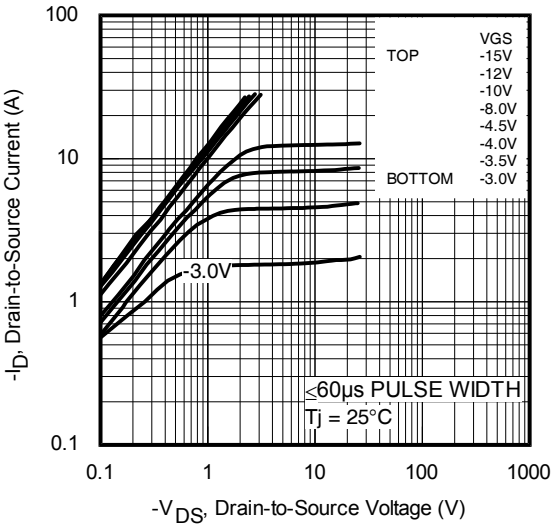


Fig. 2 Typical Output Characteristics

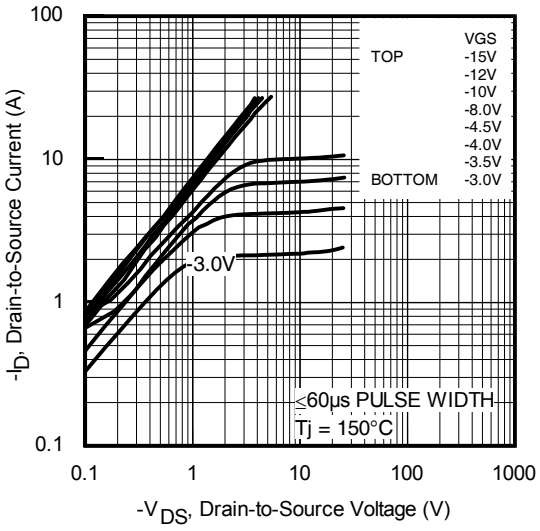


Fig. 3 Typical Output Characteristics

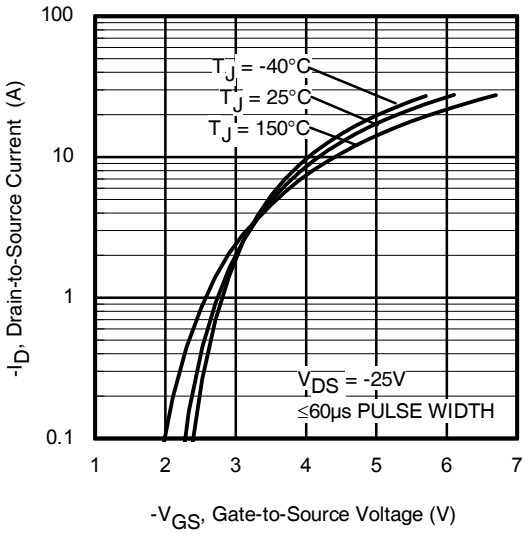


Fig. 4 Typical Transfer Characteristics

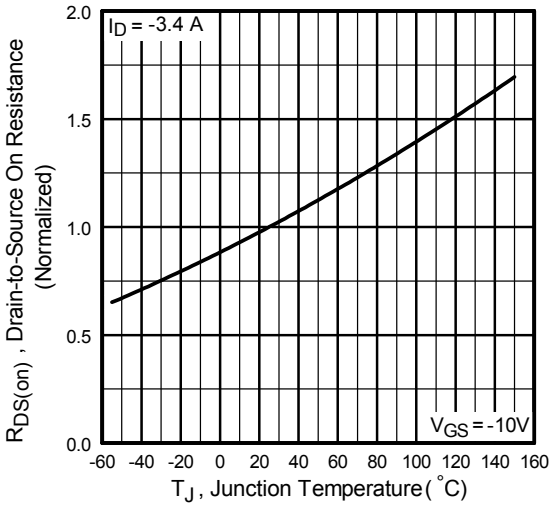


Fig 5. Normalized On-Resistance Vs. Temperature

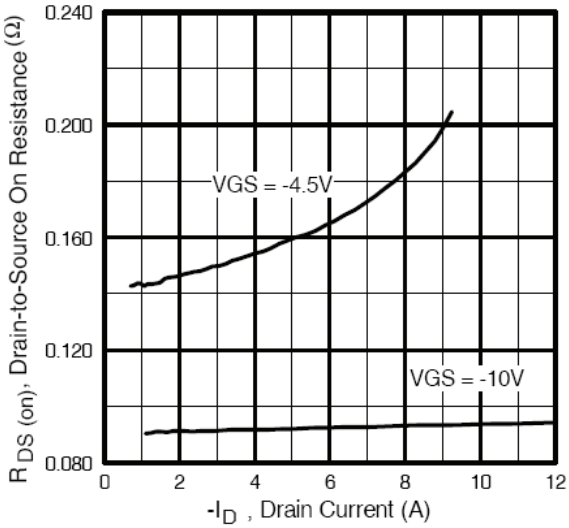


Fig 6. Typical On-Resistance Vs. Drain Current

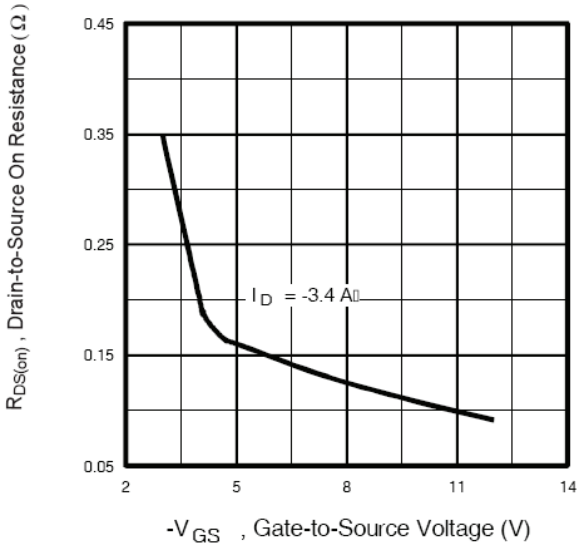


Fig. 7 Typical On-Resistance Vs. Gate Voltage

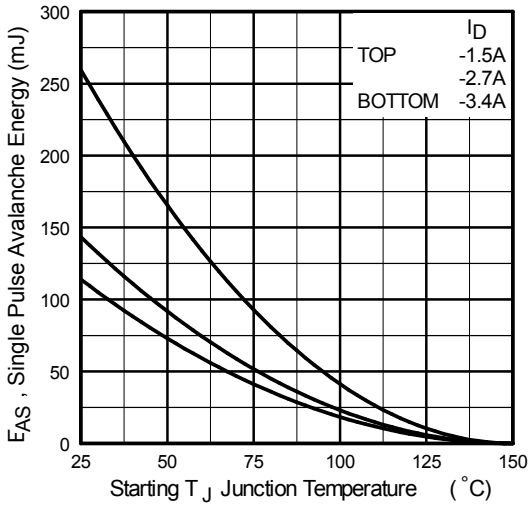


Fig 8. Maximum Avalanche Energy Vs. Drain Current

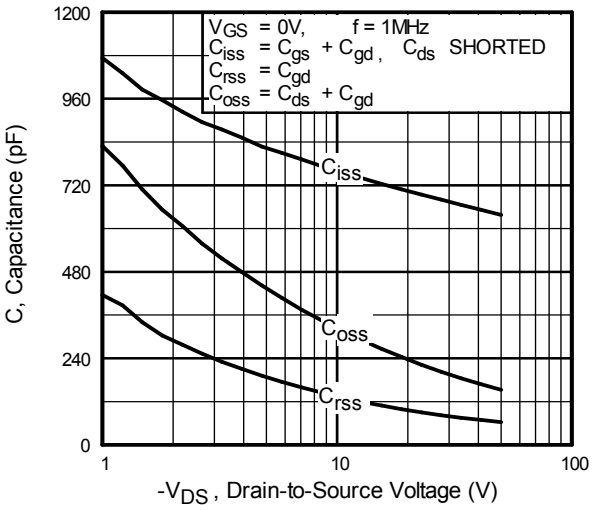


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

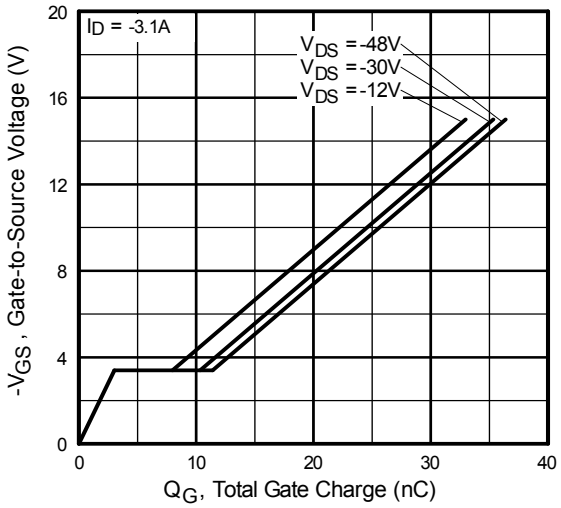


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

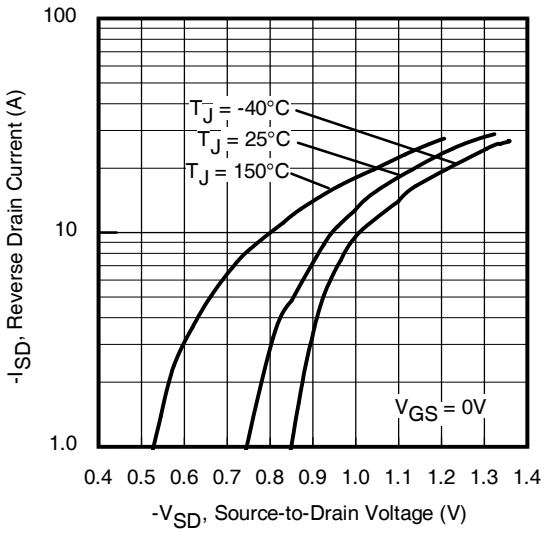


Fig. 11 Typical Source-Drain Diode Forward Voltage

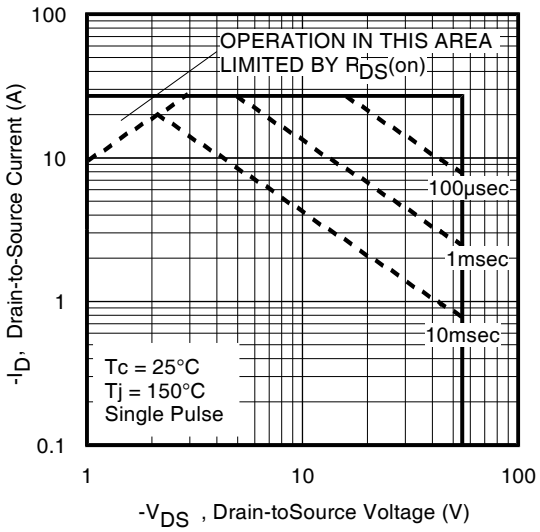


Fig. 12 Maximum Safe Operating Area

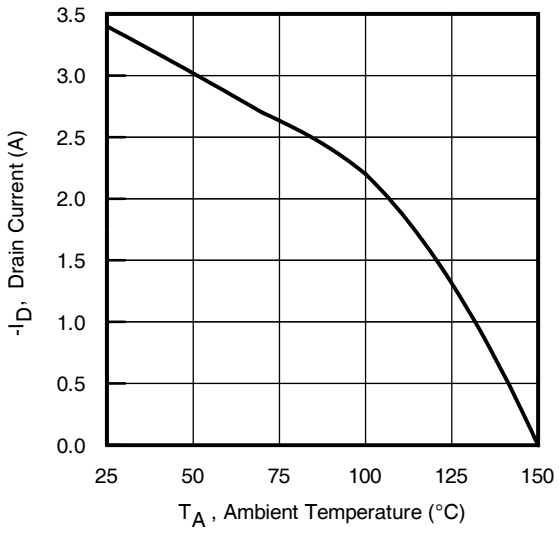


Fig 13. Maximum Drain Current vs. Ambient Temperature

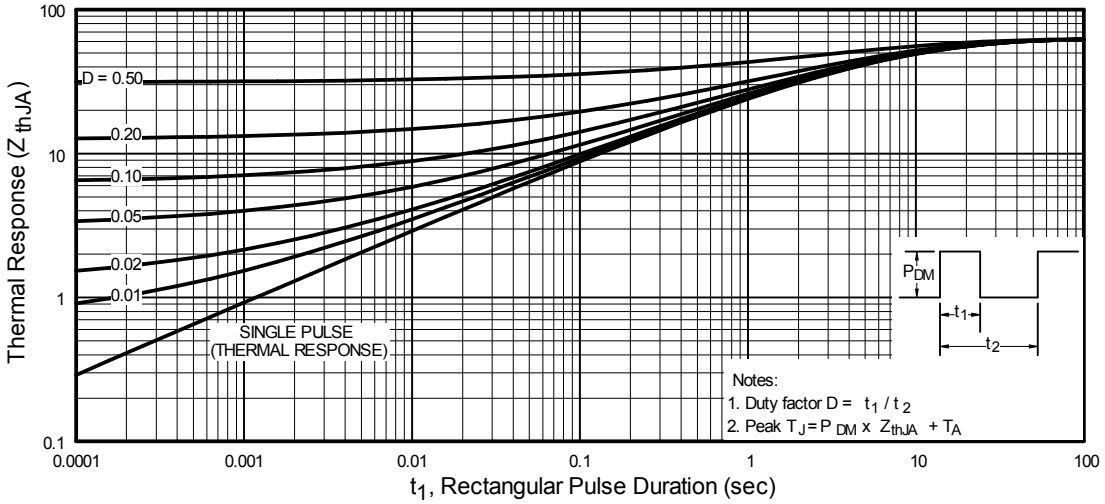
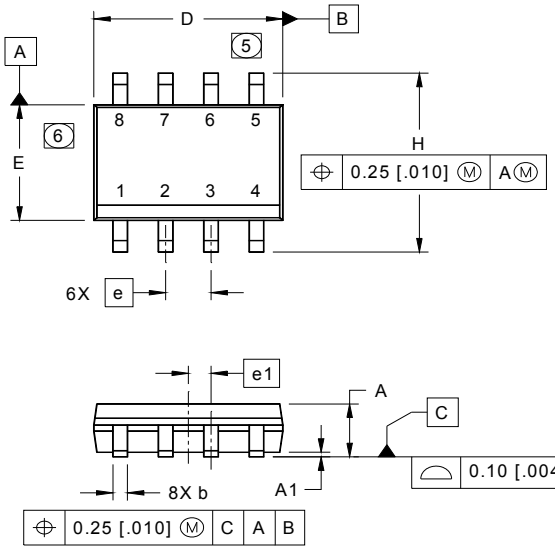
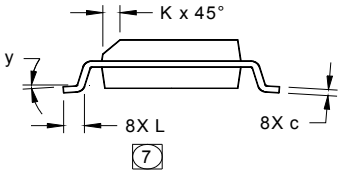


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

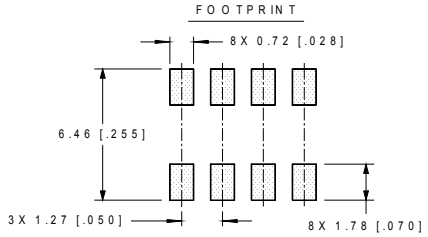
SO-8 Package Outline (Dimensions are shown in millimeters (inches)



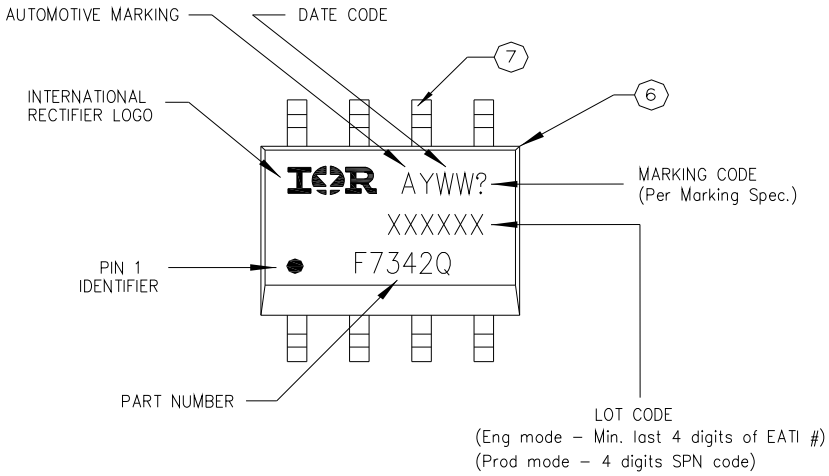
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



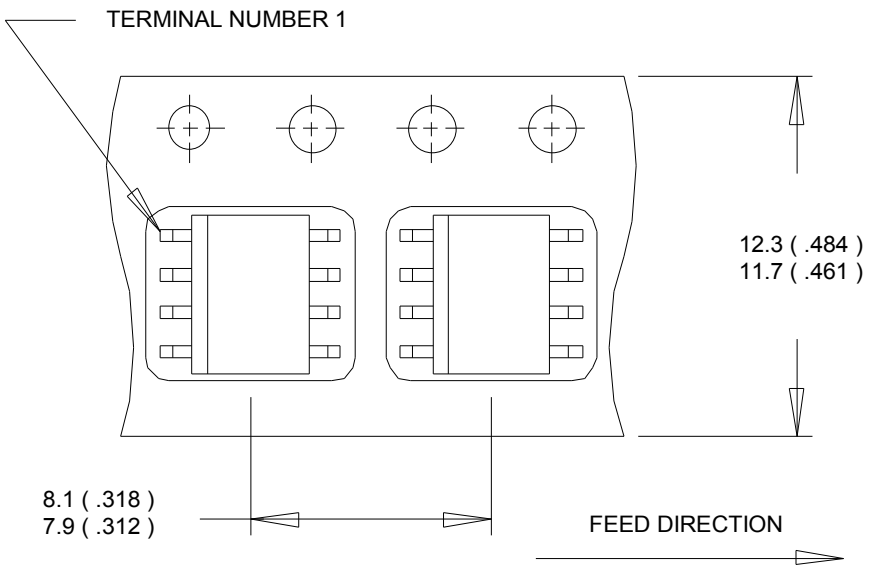
NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



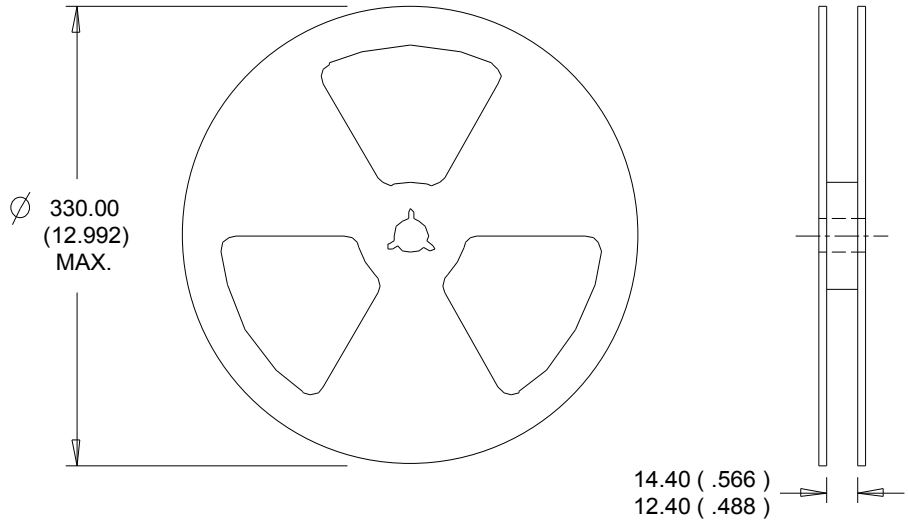
SO-8 Part Marking Information



SO-8 Tape and Reel (Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	Class M2 (+/- 200V)† AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V)† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
3/27/2014	• Added "Logic Level Gate Drive" bullet in the features section on page 1 • Updated data sheet with new IR corporate template
9/30/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.

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